

Title (en)

Substrate, substrate with thin film, semiconductor device, and method of manufacturing semiconductor device

Title (de)

Substrat, Substrat mit Dünnschicht, Halbleiterbauelement und Verfahren zur Herstellung des Halbleiterbauelements

Title (fr)

Substrat, substrat à film mince, dispositif semi-conducteur et procédé de fabrication de dispositif semi-conducteur

Publication

EP 2824223 B1 20200708 (EN)

Application

EP 14182427 A 20100406

Priority

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- EP 10764377 A 20100406
- JP 2010056206 W 20100406

Abstract (en)

[origin: US2011233562A1] A substrate achieving suppressed deterioration of processing accuracy of a semiconductor device due to bending of the substrate, a substrate with a thin film and a semiconductor device formed with the substrate above, and a method of manufacturing the semiconductor device above are obtained. A substrate according to the present invention has a main surface having a diameter of 2 inches or greater, a value for bow at the main surface being not smaller than $-40\text{ }\mu\text{m}$ and not greater than $-5\text{ }\mu\text{m}$, and a value for warp at the main surface being not smaller than $5\text{ }\mu\text{m}$ and not greater than $40\text{ }\mu\text{m}$. Preferably, a value for surface roughness Ra of the main surface of the substrate is not greater than 1 nm and a value for surface roughness Ra of a main surface is not greater than 100 nm .

IPC 8 full level

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CPC (source: EP KR US)

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